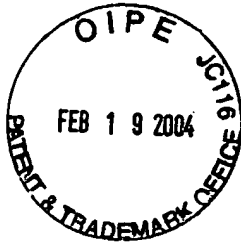


HT-01-002B



February 9, 2004

To: Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/718,878 11/21/03

Chen-Jung Chien et al.

IMPROVING JUNCTION STABILITY AND  
YIELD FOR SPIN VALVE HEADS

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

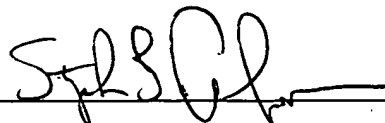
The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
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P.O. Box 1450, Alexandria, VA 22313-1450, on February 7, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 2/17/04

U.S. Patent 5,856,897 to Mauri, "Self-Biased Dual Spin Valve Sensor", discloses stabilization layers under the lead.

U.S. Patent 6,185,078 B1 to Lin et al., "Spin Valve Read Head with Antiferromagnetic Oxide Film as Longitudinal Bias Layer and Portion of First Read Gap", discloses an anti-ferromagnetic stabilization scheme employed in a magnetic head for magnetically stabilizing a free layer of a spin valve.

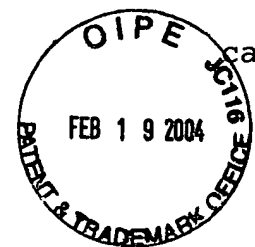
U.S. Patent 6,201,669 B1 to Kakiyama, "Magnetoresistive Element and Its Manufacturing Method", relates to a magnetoresistive element for regenerating a line of magnetically recorded information by taking advantage of an element in which electric resistance varies in response to changes of external magnetic fields.

U.S. Patent 6,208,492 B1 to Pinarbasi, "Seed Layer Structure for Spin Valve Sensor", discusses a bilayer seed layer structure employed between a first read gap layer and a spin valve sensor for increasing the magnetoresistive coefficient ( $dr/R$ ).



HT-01-002B

U.S. Patent 6,208,491 B1 to Pinarbasi, "Spin Valve with Improved Capping Layer Structure", discloses a SV with a capping structure.



Sincerely,

Stephen B. Ackerman,  
Reg. No. 37761

Form PTO-1449

Document Number (Optional)

Application Number

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)

HT-01-002B

10/718,878

Applicant

Chen-Jung Chien et al.

Filing Date

11/21/03

Group Art Unit

## U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5856897	11/5/99	Mauri	360	113	11/26/97
	6208491	3/27/01	Pinarbasi	360	324.1	5/26/99
	6185078	2/6/01	Lin et al.	360	324.12	8/21/98
	6201669	3/13/01	Kakihara	360	313	12/9/98
	6208492	3/27/01	Pinarbasi	360	324.11	5/13/99

## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Port/nort Pages, Etc.)


EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.